

Notice of References Cited	Application/Control No. 10/716,209	Applicant(s)/Patent Under Reexamination LINGUNIS ET AL.	
	Examiner Asok K. Sarkar	Art Unit 2829	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-			
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FOREIGN PATENT DOCUMENTS

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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
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